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Rhombohedral Hf_{0.5}Zr_{0.5}O₂ thin films

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Rhombohedral $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ thin films
Ferroelectricity and Devices

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Rhombohedral $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ thin films

Ferroelectricity and Devices

PhD thesis

to obtain the degree of PhD at the
University of Groningen
on the authority of the
Rector Magnificus prof. dr. E. Sterken,
and in accordance with
the decision by the College of Deans.

This thesis will be defended in public on

Friday 17 January 2020 at 16:15 hours

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To my family, friends and teachers

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